

# L-Band, GaN/SiC, RF Power Amplifier Pallet

## 1030-1090 MHz | 2200 W typ | 57% Efficiency typ | 16dB Gain typ | 50 V | Mode S ELM

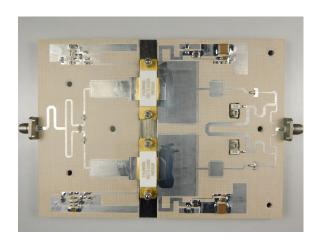
IGNP1011L2400 is a high power GaN-on-SiC RF power amplifier pallet that has been designed specifically for IFF/SSR Systems operating under either Mode S ELM [48x ( $32\mu$ s on,  $18\mu$ s off), 6.4% Long Term Duty Cycle] or standard Mode S [ $128\mu$ s, 2% Duty Cycle] pulse conditions. It supplies a minimum of 2200W of peak output power, with typically >16 dB of gain and 57% efficiency. It operates from a 50V supply voltage.

## **FEATURES**

- GaN on SiC HEMT Transistor Technology
- Matched to  $50\Omega$  at both input and output
- Suitable for both 1030 and 1090 MHz
- 100% RF Tested Under Mode S ELM pulse conditions

# **APPLICATIONS**

- L-band Avionics IFF & SSR Systems
- Suitable for both uplink and downlink (Transponder)



## Table 1. RF Electrical Characteristics (Case temperature = 25+/-5 °C unless otherwise stated)

Parameter	Symbol	Min	Тур	Max	Units	Test Conditions
Output Power	P <sub>out</sub>	2200			W	P <sub>IN</sub> = 55W
Gain	G	16			dB	f = 1030, 1090 MHz
Gain Flatness	OPF			1.5	dB	Mode S ELM pulse conditions (48 x
Drain Efficiency	η	55			%	$[32\mu s \text{ on, } 18\mu s \text{ off}]), LTDC = 6.4\%$
Pulse Droop	D	-0.6			dB	V <sub>DS</sub> = 50V, I <sub>DO</sub> = 200mA
Input Return Loss	IRL	10			dB	DS DQ
Delta Insertion Phase Variation	d-IP	-20		+20	Degrees	
Load Mismatch Stability	VSWR-S	2:1				
VSWR Withstand	VSWR-LMT	3:1				

Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.



## Table 2. Absolute Maximum Ratings (Not Simultaneous)

Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Voltage	V <sub>DS</sub>	50	V	25 °C
DC Gate-Source Voltage	V <sub>GS</sub>	-8 to +1	V	25 °C
DC Drain Current	I <sub>D</sub>	85	A	25 °C
DC Gate Current	I <sub>G</sub>	TBD	mA	25 °C
RF Input Power	P <sub>RF,IN</sub>	55	W	25 °C
Storage Temperature	T <sub>stg</sub>	-55 to +150	0°C	

Note: Operation outside the limits given in this table may cause permanent damage to the module

#### Table 3. DC Electrical Characteristics (Case temperature = 25+/-2 °C unless otherwise stated)

Parameter	Symbol	Min	Тур	Max	Units	Test Conditions
Drain-Gate Breakdown Voltage BV <sub>DG</sub> 150		150			V	Source terminal open, $I_{DG}$ = 4mA
Gate Pinch-Off Voltage	V <sub>P</sub>	-5			V	$V_{_{\rm DS}} = 50V, I_{_{\rm DS}} = 1mA$
Quiescent Gate Voltage	V <sub>Q</sub>		-2.6		V	V <sub>DS</sub> = 50V, I <sub>DS</sub> = 200mA

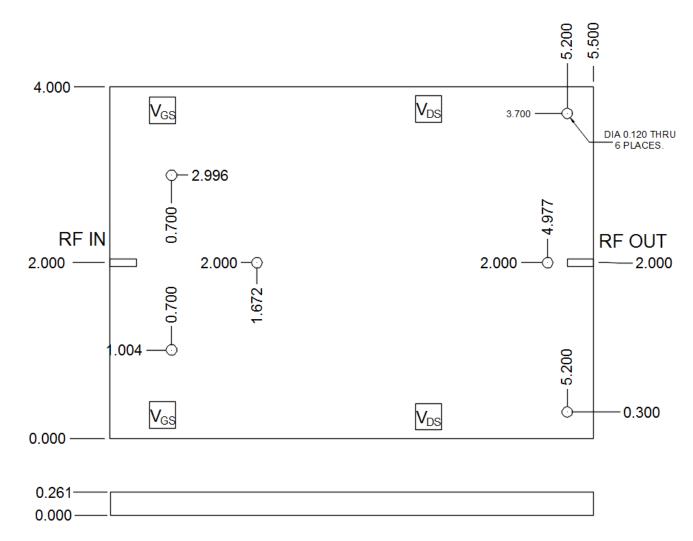
#### Table 4. Thermal Resistance (Case temperature = 25+/-5 °C unless otherwise stated)

Parameter	Symbol	Min	Тур	Max	Units	Test Conditions
Peak Thermal Resistance, channel to underneath side of module	R <sub>th</sub>		TBD		°C/W	$\begin{split} P_{_{OUT}} &= 2200W \\ f &= 1030, 1090 \text{ MHz} \\ \text{Mode S ELM pulse conditions (48 x [32 \mu s on, 18 \mu s off]), LTDC = 6.4\% } \\ V_{_{DS}} &= 50V, I_{_{DQ}} = 200\text{mA} \end{split}$

## Table 5. Typical Performance

Freq (MHz)	V <sub>DD</sub> (V)	P <sub>iN</sub> (₩)	IRL (dB)	Р <sub>оит</sub> (W)	G <sub>P</sub> (dB)	I <sub>d</sub> (A)	N <sub>c</sub> (%)	Droop (dB)
1030	50	55.0	11.0	2232	16.08	77.09	57.84	-0.23
1090	50	55.0	14.0	2214	16.05	77.5	57.14	-0.13





**Dimensions: Inches** 



#### **ESD** Rating

Parameter Rating		Standard				
ESD Human Body Model (HBM) TBD		ESDA/JEDEC JS-001-2012				
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C101F				
Moisture Sensitivty Level (MSL)	0	IPC/JEDEC J-STD-020				

DEFINITIONS: DATA SHEET STATUS

Advanced Specification - This data sheet contains Advanced specifications.

Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications.

MAXIMUM RATINGS Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability. DISCLAIMER: Integra Technologies Inc. makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Integra Technologies Inc. assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. Integra Technologies Inc. products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Integra Technologies Inc. customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Integra Technologies Inc. for any damages resulting from such improper use or sale. Copyright © 2018.

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